**CNSE NanoFab Tool Calibration Form**

**DATE: \_\_2/23/2016\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_**

**Tool Description: \_\_\_\_STS Multiflex RIE\_\_**

**Test: PECVD silicon dioxide etch rate**

**Run Parameters:**

**Sample size: 4” silicon wafer**

**Mask: Shipley 1813 final spin at 4K rpm**

**Edge bead removal**

**Etch Condition: 100 mT chamber pressure**

 **CHF3: 40 sccm**

 **CF4: 10 sccm**

 **300 W RF**

**PECVD silicon dioxide etch rate: 219 nm / min**

**Etch Profile: 80 degrees (estimated)**

**Oxide to photo resist selectivity: 5:1**

**Etch Uniformity: 1.3 %**

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**Engineer: CNSE Staff\_Frank Lee\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_\_**